

**Notice of References Cited**Application/Control No.  
10/069,951Applicant(s)/Patent Under  
Reexamination  
GAUCHER, PHILIPPEExaminer  
Kripa SagarArt Unit  
1756

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4,541,855	09-1985	Scherer, George W.	65/395
	B	US-5,100,764	03-1992	Paulson et al.	430/311
	C	US-5,494,700	02-1996	Anderson et al.	427/115
	D	US-5,944,866	08-1999	Chen et al.	65/395
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Tohge, N. et al., "Ferroelectric properties of PLZT films prepared by the sol-gel process using chemically modified metal-alkoxides", JI. of Mat.Sc and matl. in Elect., v.5 (1994), p.356-359
	V	Tohge, N. et al., "Preparation of PbZrO <sub>3</sub> -PbTiO <sub>3</sub> Ferroelectric Thin Films by the Sol-Gel Process", JI.Am.Cer.Soc. v74(1),(1991), p. 67-71
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.